1A, 600V- 1000V Standard Bridge Rectifier

FEATURES

TAIWAN

Glass passivated chip junction

SEMICONDUCTOR

- Ideal for automated placement
- Reliable low cost construction utilizing molded plastic technique
- High surge current capability
- UL Recognized File # E-326854
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS) •
- Adapters •
- Lighting application •

MECHANICAL DATA

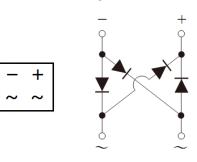
- Case: ABS
- Molding compound meets UL 94V-0 flammability rating •
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 0.120g (approximately)

| KEY PARAMETERS | | | | |
|--------------------|------------|---|--|--|
| PARAMETER VALUE UN | | | | |
| ١ _F | 1 | А | | |
| V _{RRM} | 600 - 1000 | V | | |
| I _{FSM} | 30 A | | | |
| T _{J MAX} | 150 °C | | | |
| Package | ABS | | | |
| Configuration | Quad | | | |





ABS



| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted) | | | | | | | |
|---|--------------|------------------------|------------------|--------|------------------|------|---|
| PARAMETER | | SYMBOL | ABS6-T | ABS8-T | ABS10-T | UNIT | |
| Marking code on the device | | | ABS6 | ABS8 | ABS10 | | |
| Repetitive peak reve | erse voltage | e | V _{RRM} | 600 | 800 | 1000 | V |
| Reverse voltage, total rms value | | V _{R(RMS)} | 420 | 560 | 700 | V | |
| Forward current On glass-epoxy On aluminum substrate | | I _F | 0.8 | | Α | | |
| | | | 1.0 | | Α | | |
| Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ | | | 30 | | Α | | |
| | | T _J = 125°C | I _{FSM} | 25 | | | Α |
| Peak forward surge current, $T_J = 25^{\circ}C$ | | 1 | 60 | | Α | | |
| 1.0 single half sine-wave superimposed on rated load $T_J = 125^{\circ}C$ | | I _{FSM} | 50 | | | Α | |
| Rating for fusing (t<8.3ms) | | l ² t | 3.74 | | A ² s | | |
| Junction temperature | | TJ | - 55 to +150 | | °C | | |
| Storage temperature | | T _{STG} | - 55 to +150 | | °C | | |



| THERMAL PERFORMANCE | | | | |
|--|------------------|-----|------|--|
| PARAMETER | SYMBOL | ТҮР | UNIT | |
| Junction-to-lead thermal resistance | R _{ejl} | 25 | °C/W | |
| Junction-to-ambient thermal resistance | R _{eja} | 80 | °C/W | |

| ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted) | | | | | |
|--|---------------------------------|----------------|-----|------|------|
| PARAMETER | CONDITIONS | SYMBOL | ТҮР | MAX | UNIT |
| Forward voltage per diode ⁽¹⁾ | $I_F = 0.4A, T_J = 25^{\circ}C$ | V _F | - | 0.95 | V |
| $\mathbf{P}_{\text{overse overset}} \otimes \operatorname{reted} \mathcal{V}$, per diado ⁽²⁾ | $T_J = 25^{\circ}C$ | I | - | 10 | μA |
| Reverse current @ rated V_R per diode ⁽²⁾ | T _J = 125°C | IR | - | 150 | μA |

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

| ORDERING INFORMATION | | | | |
|--|-----|---------------------|--|--|
| ORDERING CODE ⁽¹⁾ PACKAGE PACKING | | | | |
| ABSx-T | ABS | 5,000 / Tape & Reel | | |

Notes:

1. "x" defines voltage from 600V(ABS6-T) to 1000V(ABS10-T)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

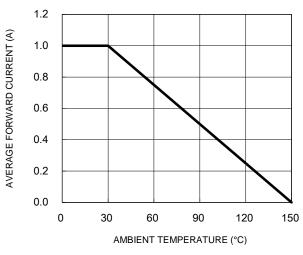


Fig.1 Forward Current Derating Curve

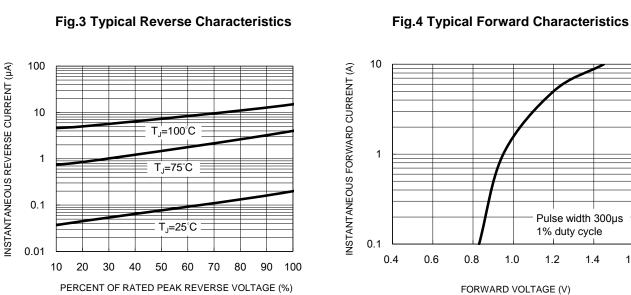


Fig.5 Maximum Non-Repetitive Forward Surge Current

1000

100

10

0.1

11111

1

f=1.0MHz Vsig=50mVp-p

CAPACITANCE (pF)

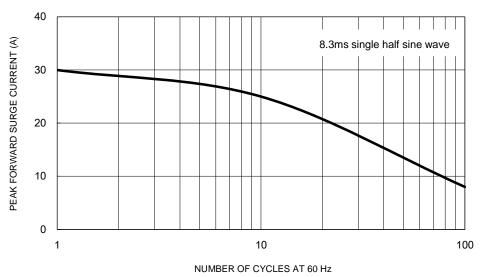


Fig.2 Typical Junction Capacitance

10

REVERSE VOLTAGE (V)

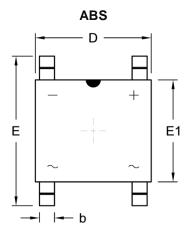
100

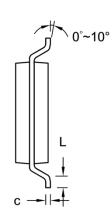
1000

1.6

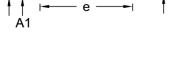


PACKAGE OUTLINE DIMENSIONS





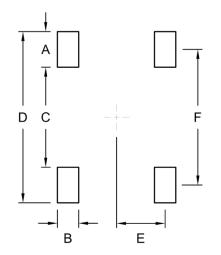
| DIM. | Unit (mm) | | Unit | (inch) |
|------|-----------|------|-------|--------|
| | Min. | Max. | Min. | Max. |
| A | 1.40 | 1.60 | 0.055 | 0.063 |
| A1 | 0.05 | 0.15 | 0.002 | 0.006 |
| A2 | 1.35 | 1.45 | 0.053 | 0.057 |
| b | 0.60 | 0.70 | 0.024 | 0.028 |
| с | 0.15 | 0.25 | 0.006 | 0.010 |
| D | 4.90 | 5.10 | 0.193 | 0.201 |
| E | 6.25 | 6.65 | 0.246 | 0.262 |
| E1 | 4.30 | 4.50 | 0.169 | 0.177 |
| е | 3.90 | 4.10 | 0.154 | 0.161 |
| L | 0.30 | 0.70 | 0.012 | 0.028 |



1

А

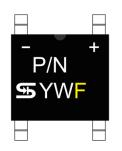
SUGGESTED PAD LAYOUT



A2

| Symbol | Unit (mm) | Unit (inch) |
|--------|-----------|-------------|
| А | 1.50 | 0.059 |
| В | 0.90 | 0.035 |
| С | 4.22 | 0.166 |
| D | 7.22 | 0.284 |
| E | 2.05 | 0.081 |
| F | 5.72 | 0.225 |

MARKING DIAGRAM



- P/N = Marking Code
- YW = Date Code
- F = Factory Code



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